

<b>SANYO</b>	No.5266	2SJ416
		P-Channel Silicon MOSFET
<b>Ultrahigh-Speed Switching Applications</b>		

**Features**

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

**Absolute Maximum Ratings at Ta = 25°C**

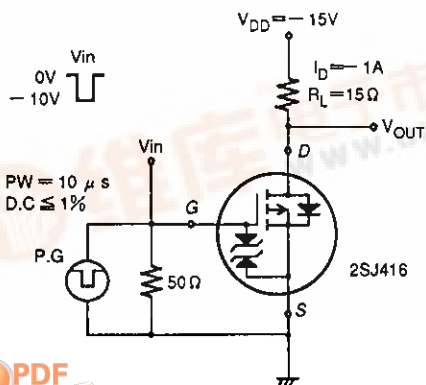
			unit
Drain-to-Source Voltage	V <sub>DSS</sub>	-30	V
Gate-to-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current(DC)	I <sub>D</sub>	-2	A
Drain Current(Pulse)	I <sub>DP</sub>	PW ≤ 10μs, duty cycle ≤ 1%	-8 A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on ceramic board (250mm <sup>2</sup> × 0.8mm) Tc = 25°C	1.5 W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

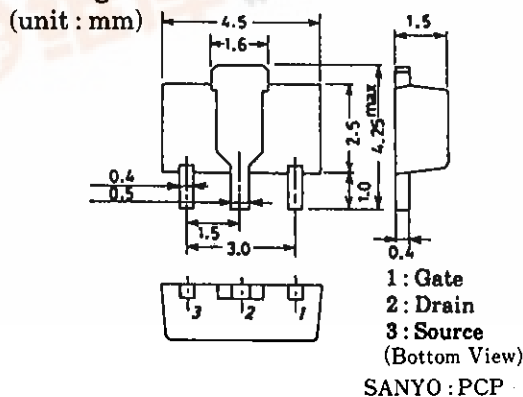
			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1mA, V <sub>GS</sub> = 0	-30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0			-100	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA	-1.0		-2.5	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1A	1.2	2.0		S
Static Drain-to-Source ON-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = -1A, V <sub>GS</sub> = -10V		310	440	mΩ
	R <sub>DS(on)</sub>	I <sub>D</sub> = -1A, V <sub>GS</sub> = -4V		480	650	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		170		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		120		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		30		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		10		ns
Rise Time	t <sub>r</sub>	"		20		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	"		110		ns
Fall Time	t <sub>f</sub>	"		75		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -2A, V <sub>GS</sub> = 0	-1.0	-1.2		V

Marking : JJ

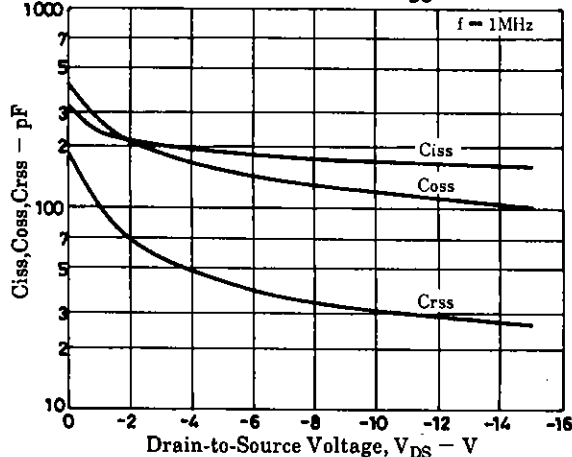
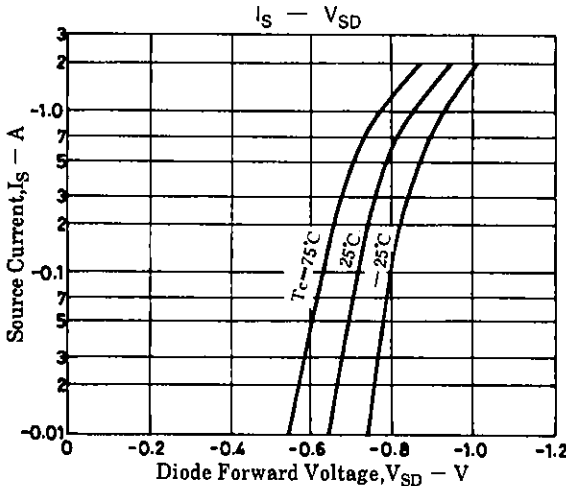
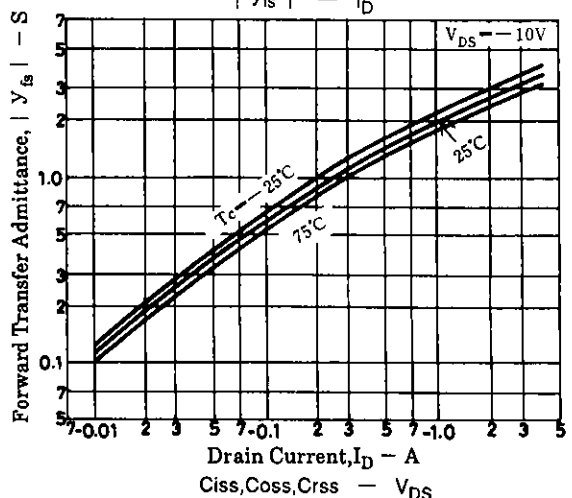
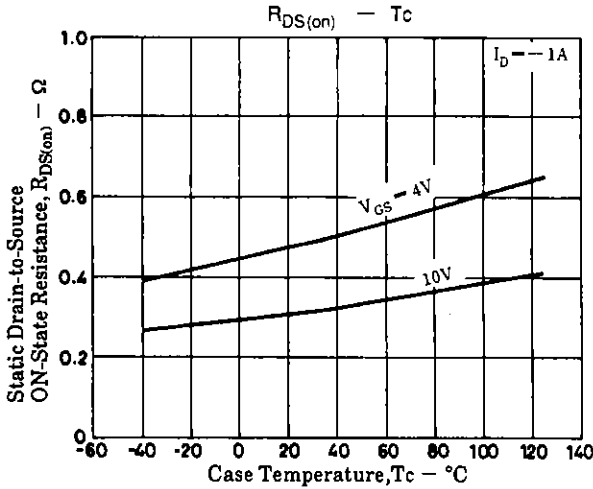
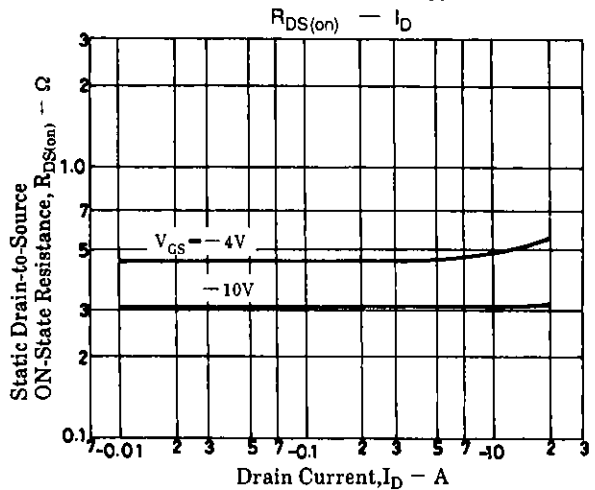
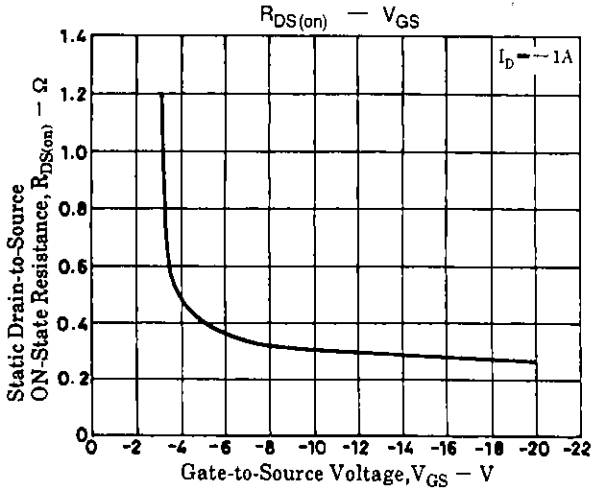
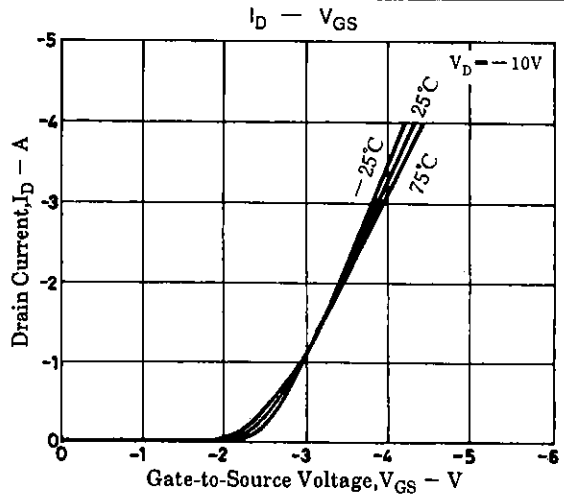
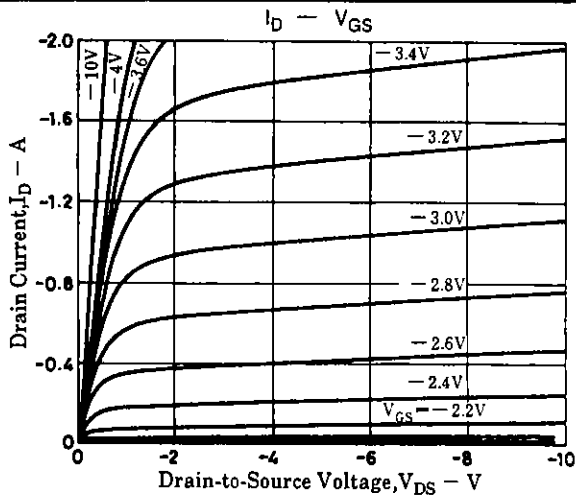
**Switching Time Test Circuit**

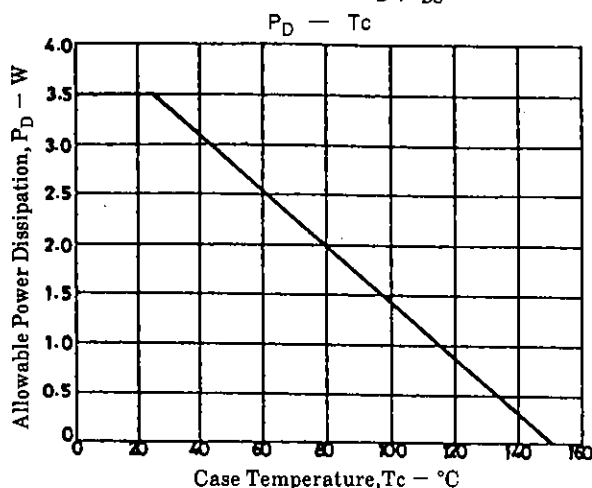
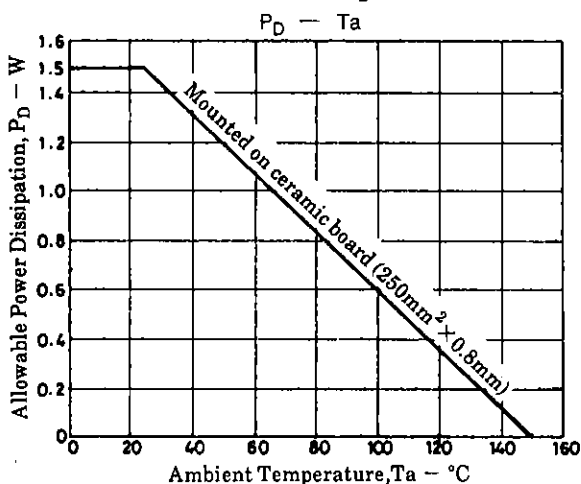
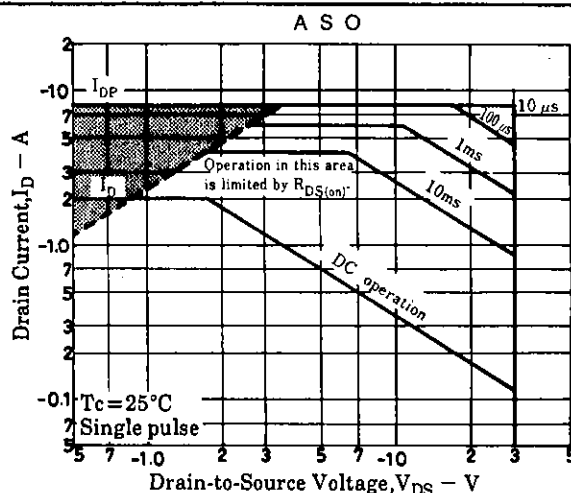
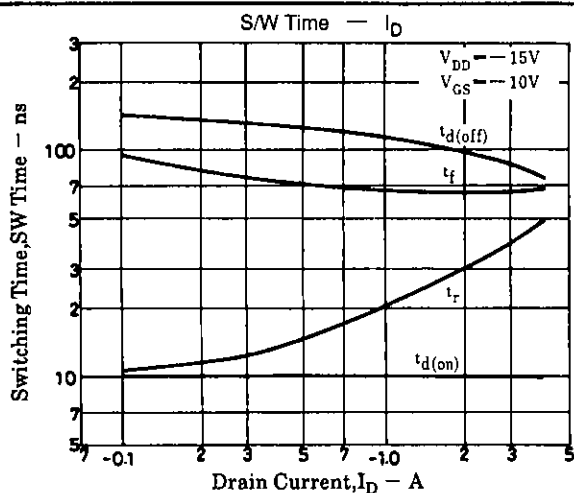


**Package Dimensions 2062A**



2SJ416





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